



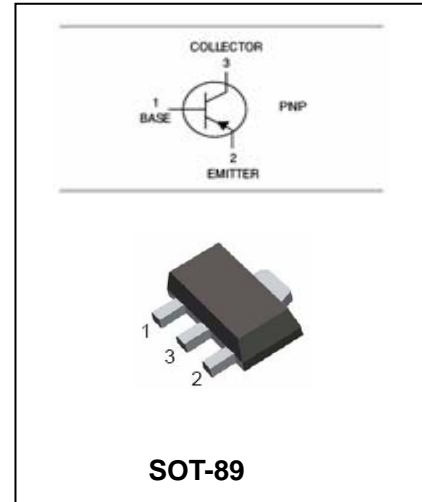
## 2SB1260

### FEATURES

- High breakdown voltage and high current.  
 $BV_{CEO}=-80V, I_C=-1A$
- Good  $h_{FE}$  Linearity.
- Low  $V_{CE(sat)}$ .
- Complements the 2SD1898.

### APPLICATIONS

- Epitaxial planar type PNP silicon transistor



### ORDERING INFORMATION

Type No.	Marking	Package Code
2SB1260	ZL	SOT-89

### MAXIMUM RATING @ $T_a=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-80	V
$V_{CEO}$	Collector-Emitter Voltage	-80	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -DC -Pulse	-1 -2	A
$P_c$	Collector power Dissipation	0.5 2 * <sub>1</sub>	W
$T_j$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature	-55 to +150	$^{\circ}C$

\*1: When mounted on a 40\*40\*0.7mm ceramic board.

# Power Transistor(-80V,-1A)

# 2SB1260

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A$ $I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA$ $I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A$ $I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-60V$ $I_E=0$			-1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-4V$ , $I_C=0$			-1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=-3V$ $I_C=-0.1A$	120		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA$ $I_B=-50mA$			-0.4	V
Output Capacitance	$C_{obo}$	$V_{CB}=-10V$ $f=1.0MHz$ $I_E=0$	-	20		pF

## CLASSIFICATION $h_{FE}$

Rank	Q	R
Range	120-270	180-390

# Power Transistor(-80V,-1A)

# 2SB1260

## TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

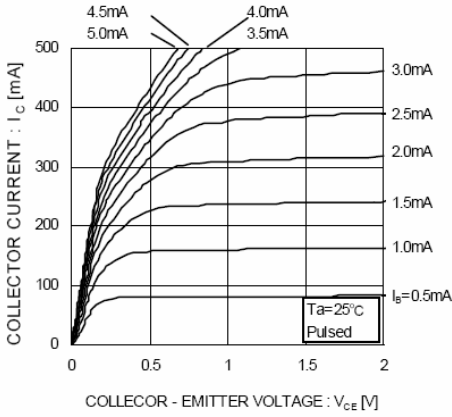


Fig.1 Ground Emitter Output Characteristics

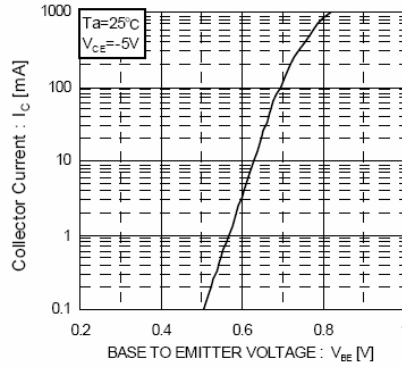


Fig.2 Grounded Emitter Propagation Characteristics

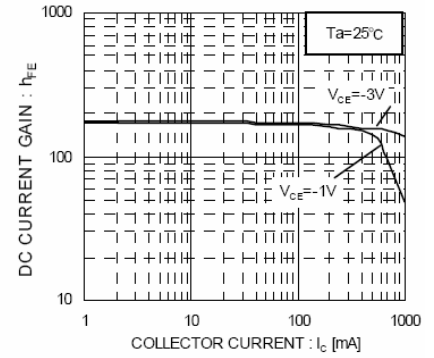


Fig.3 DC Current Gain vs Collector Current

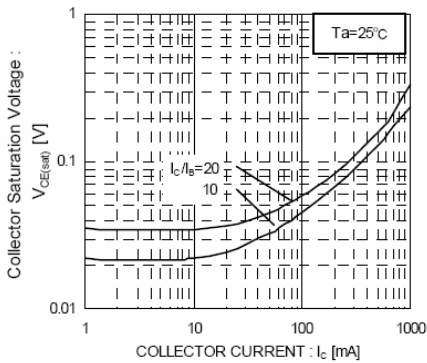


Fig.4 Collector-Emitter Saturation Voltage vs Collector Current

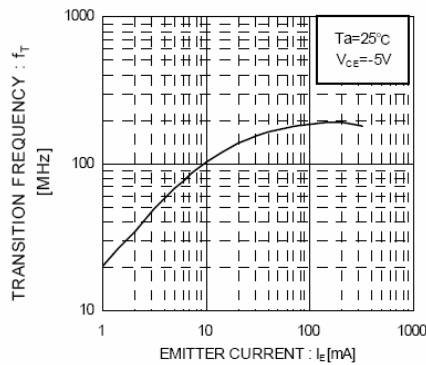


Fig.5 Transition Frequency vs Emitter Current

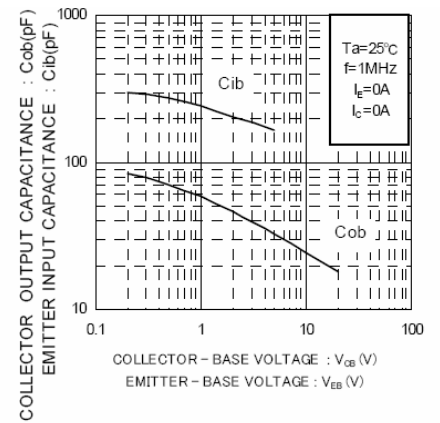


Fig.6 Emitter Input Capacitance vs. Emitter-Base Voltage  
Collector Output Capacitance vs. Collector-Base

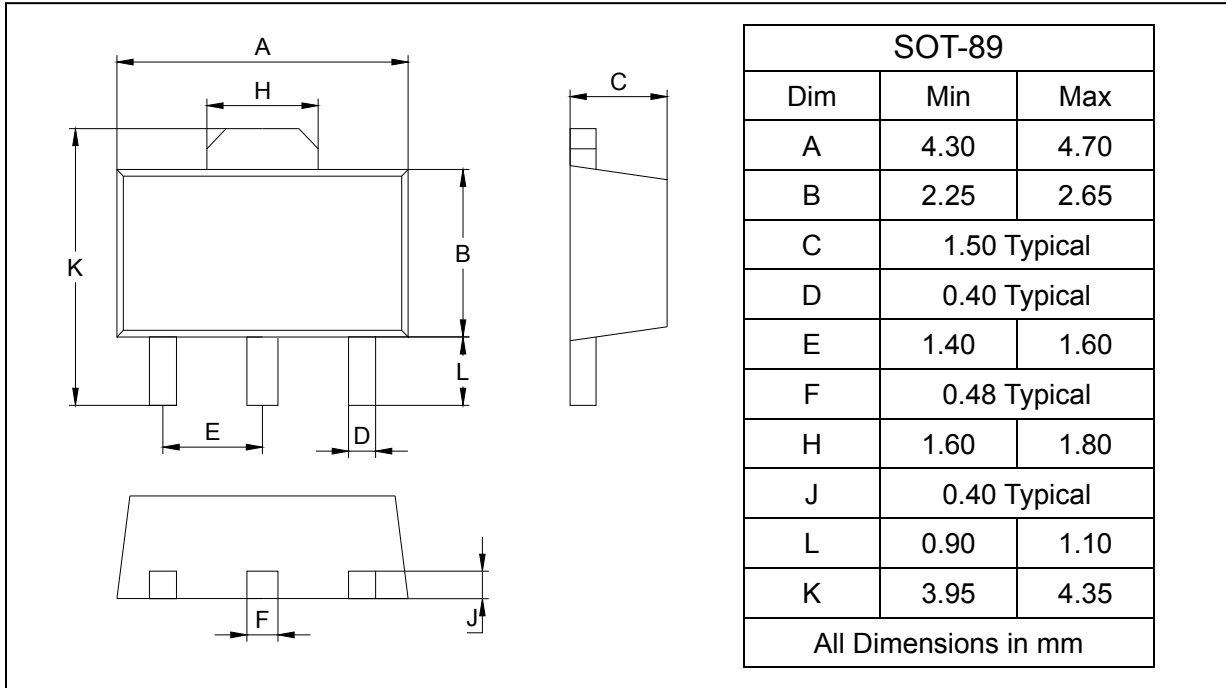
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**2SB1260**

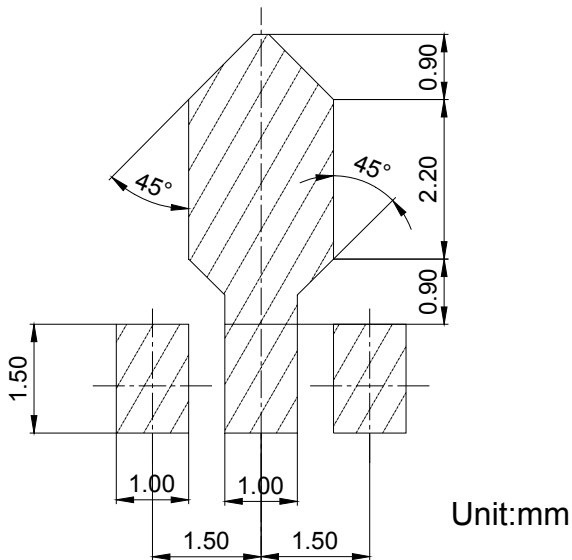
## PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



## SOLDERING FOOTPRINT



## PACKAGE INFORMATION

Device	Package	Shipping
2SB1260	SOT-89	1000/Tape&Reel